

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Jin-Koo Rhee et al.

Serial No:

09/755,436

Filed:

January 4, 2001

For:

TRANSISTOR WITH π GATE

STRUCTURE AND METHOD FOR

PRODUCING THE SAME

<u>AMENDMENT</u>

Box Non-Fee Assistant Commissioner for Patents Washington, D.C. 20231

Art Unit:

2827

Examiner:

Luan C. Thai

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Assistant Commissioner for Patents Washington D.C. 20231, on January 2 , 2003 Date of Deposit Amit Sheth Name 01/ 2 /03

Signature

Date

Dear Sir:

In response to the Office Action dated October 4, 2002, in connection with the above-

identified application, please enter and consider the following amendments and remarks:

IN THE ABSTRACT:

Please substitute the abstract of the disclosure originally filed with the present application with the substitute abstract attached hereto.

Please amend claim 1 and add new claims 3-6 as follows:

Please substitute the claims listed below for the pending claims with the same number:

## Marked-Up Claim:

(Amended) A transistor [with  $\pi$  – gate structure, with a GaAs wafer formed on 1. the bottom with GND, which is grounded to source layers formed on the top surface of the GaAs wafer by the process of back side via-hole, with a drain formed between the source layers, the top part of which has an air-layer, and with a gate shaped, as the result of using the air bridge